

Description

The HM35N03Q uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

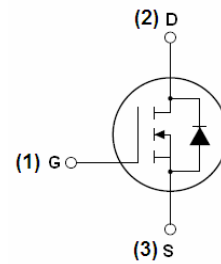
General Features

- $V_{DS} = 30V, I_D = 35A$
 $R_{DS(ON)} = 4.8m\Omega$ (Typ) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 7.5m\Omega$ (Typ) @ $V_{GS} = 4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

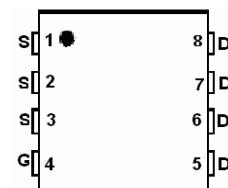
Application

- Secondary side synchronous rectifier
- High side switch in POL DC/DC converter

100% UIS TESTED!



Schematic diagram



DFN 3x3 EP top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM35N03Q	HM35N03Q	DFN 3x3 EP	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	35	A
Pulsed Drain Current	I_{DM}	120	A
Maximum Power Dissipation	P_D	35	W
Derating factor		0.28	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	150	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.6	°C/W
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Electrical Characteristics (TC=25°C unless otherwise noted)

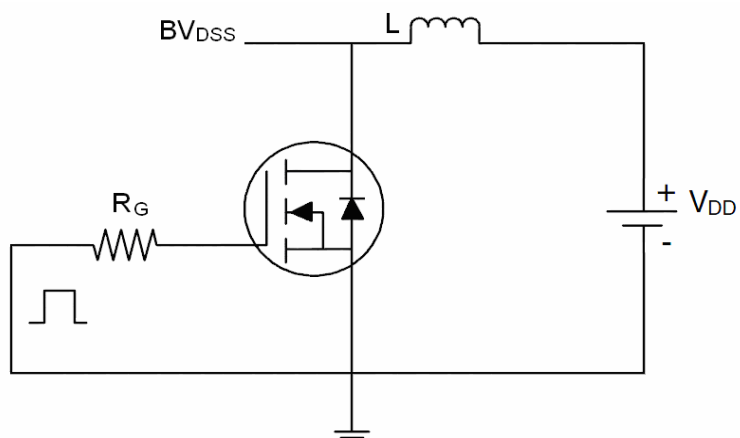
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	4.8	6.2	mΩ
		V _{GS} =4.5V, I _D =10A	-	7.5	12	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =12A	30	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	1265	-	PF
Output Capacitance	C _{oss}		-	600	-	PF
Reverse Transfer Capacitance	C _{rss}		-	130	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =12A V _{GS} =10V, R _{GEN} =6Ω	-	18	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =12A, V _{GS} =10V	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	2.7	-	nC
Gate-Drain Charge	Q _{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =12A	-	0.85	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	25	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 12A di/dt = 100A/μs(Note3)	-	-	47	nS
Reverse Recovery Charge	Q _{rr}		-	-	25	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

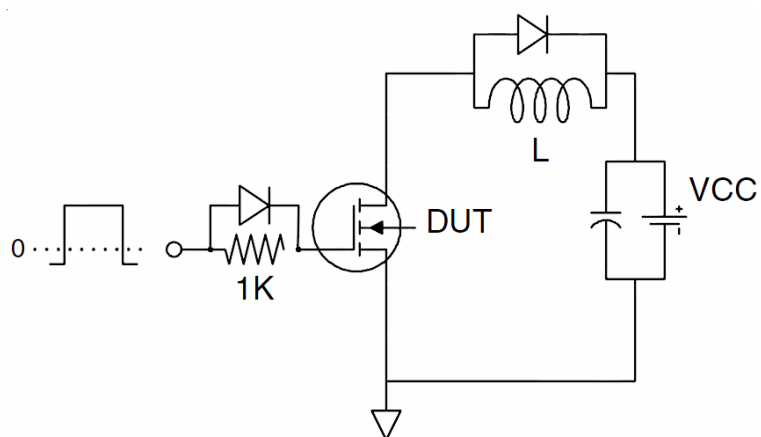
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.1mH, R_g=25\Omega$

Test Circuit

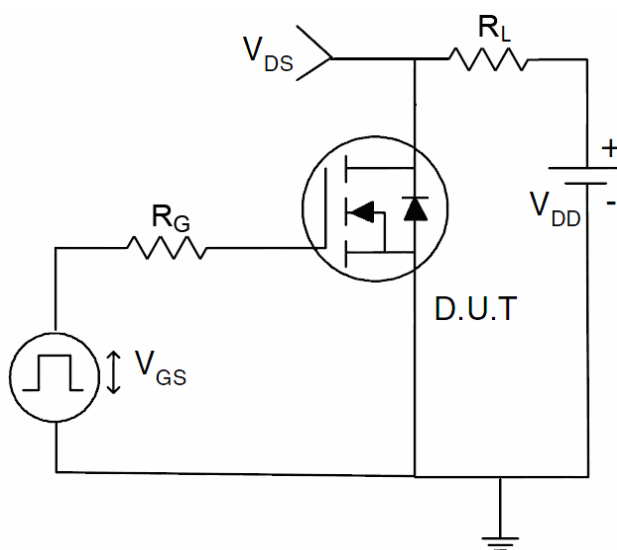
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

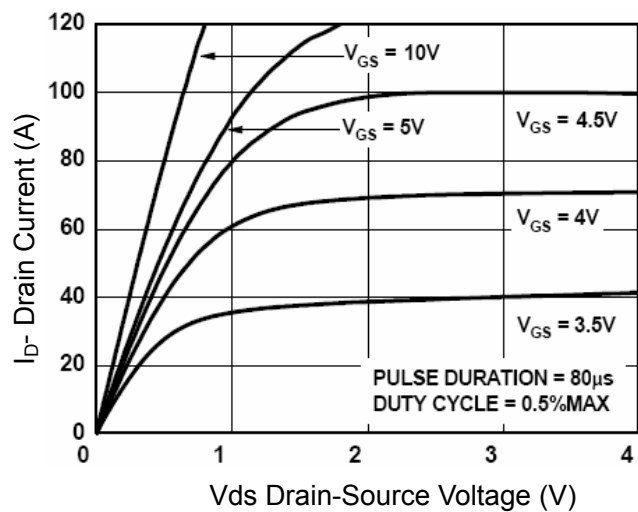


Figure 1 Output Characteristics

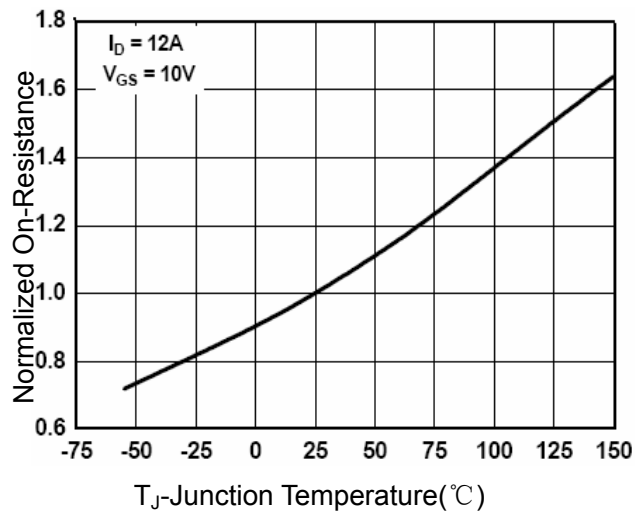


Figure 4 $R_{DS(on)}$ -Junction Temperature

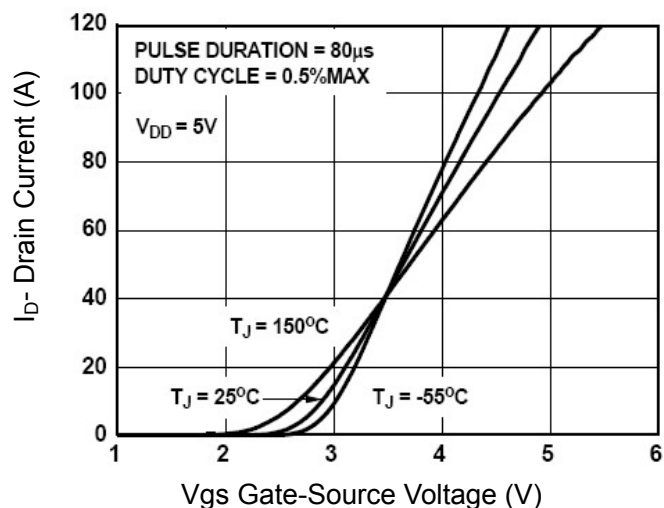


Figure 2 Transfer Characteristics

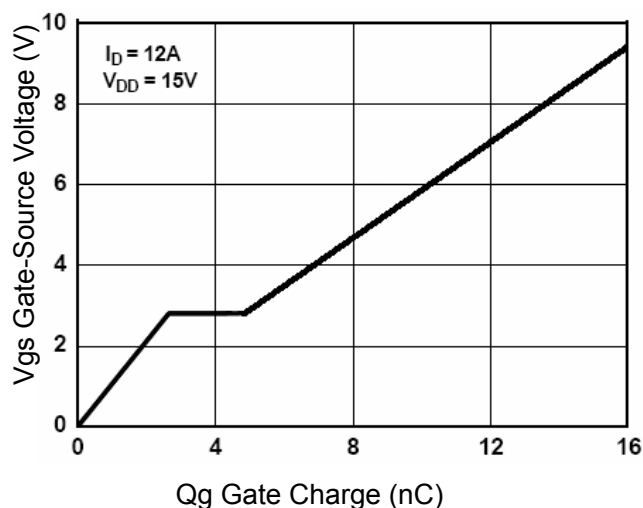


Figure 5 Gate Charge

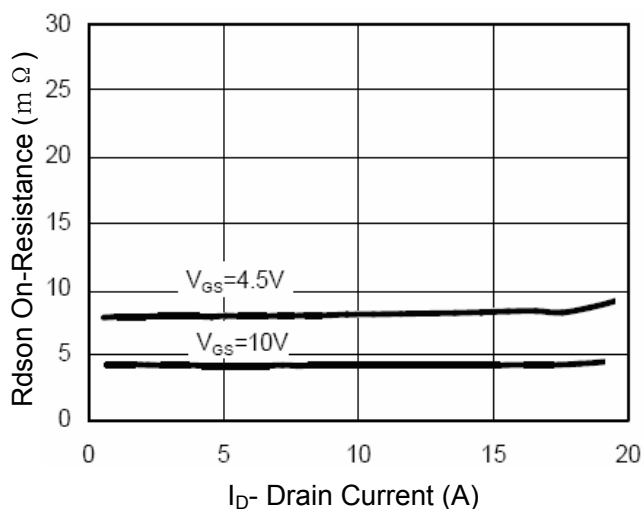


Figure 3 $R_{DS(on)}$ - Drain Current

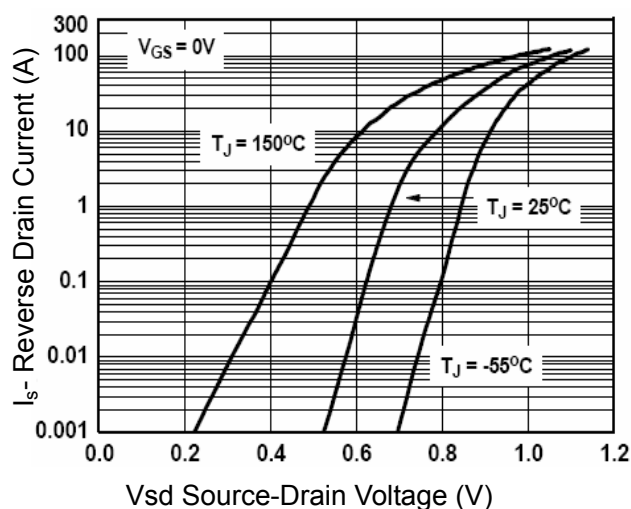
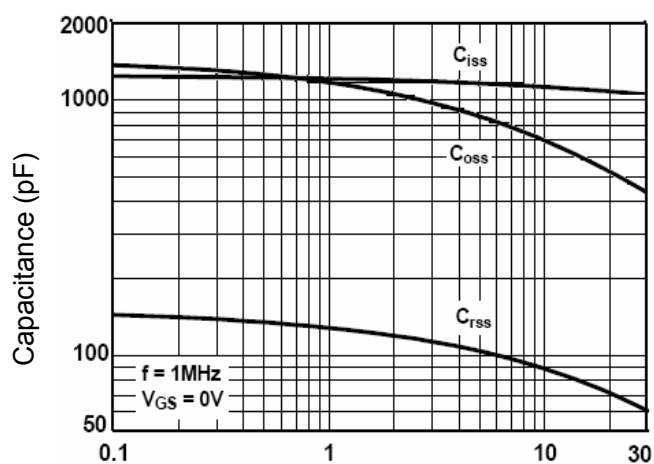
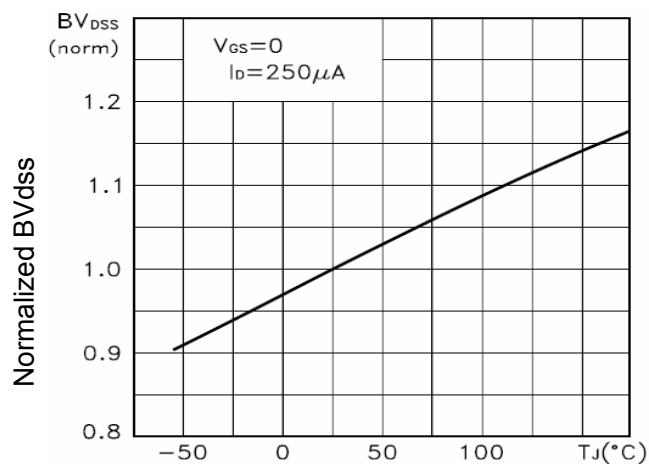


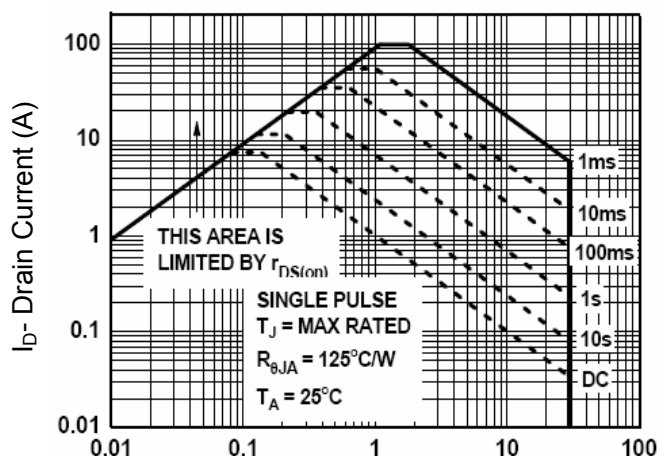
Figure 6 Source- Drain Diode Forward



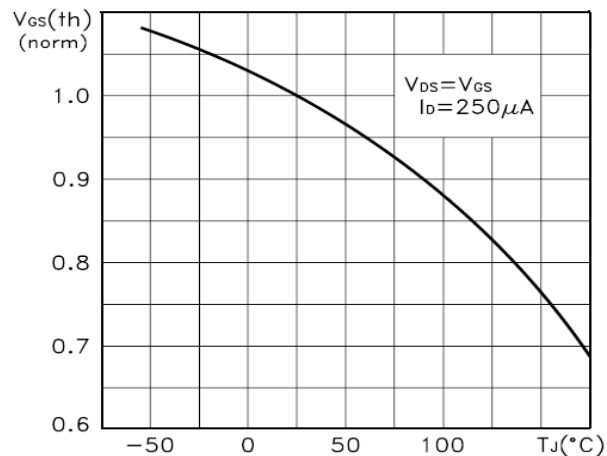
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



T_J-Junction Temperature(°C)
Figure 9 BV_{DSS} vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)
Figure 10 V_{GS(th)} vs Junction Temperature

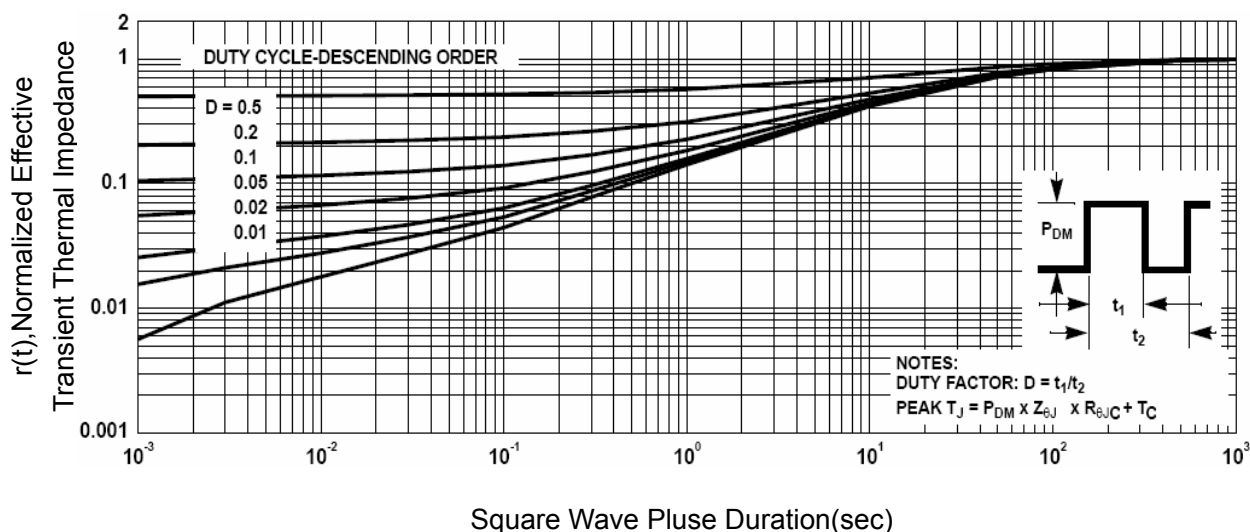
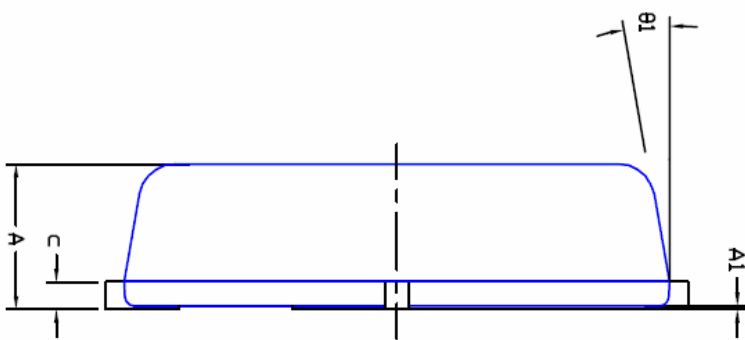
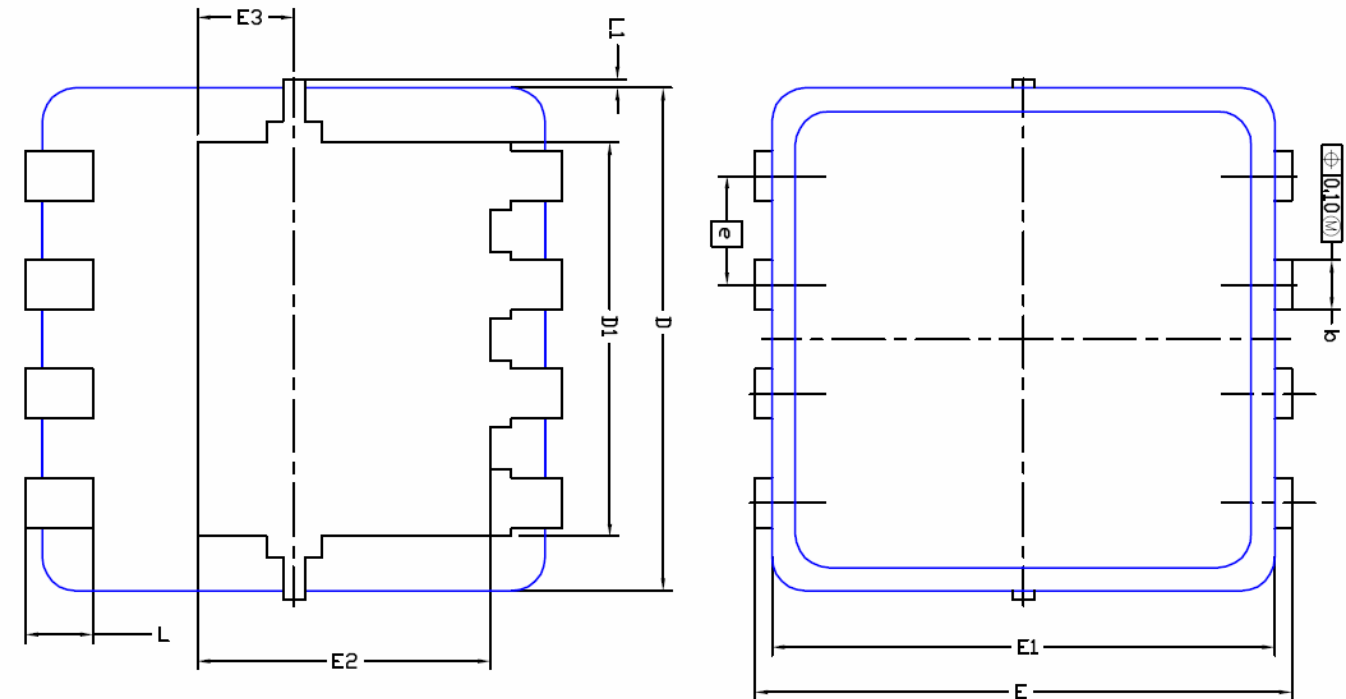


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°